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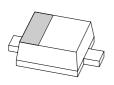
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Team Nexperia



200 mA low V_F MEGA Schottky barrier rectifier Rev. 01 — 15 May 2009 P

Product data sheet

Product profile 1.

1.1 General description

Planar Maximum Efficiency General Application (MEGA) Schottky barrier rectifier with an integrated guard ring for stress protection, encapsulated in a SOD323F (SC-90) small and flat lead Surface-Mounted Device (SMD) plastic package.

1.2 Features

- Average forward current: I_{F(AV)} ≤ 0.2 A
- Reverse voltage: $V_R \le 60 V$
- Low forward voltage
- AEC-Q101 qualified
- Small and flat lead SMD plastic package

1.3 Applications

- Low voltage rectification
- High efficiency DC-to-DC conversion
- Switch Mode Power Supply (SMPS)
- Reverse polarity protection
- Ultra high-speed switching
- Low power consumption applications

1.4 Quick reference data

Table 1. Quick reference data

 $T_i = 25 \circ C$ unless otherwise specified.

)	1					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
I _{F(AV)}	average forward current	square wave; $\delta = 0.5$; f = 20 kHz				
		$T_{amb} \le 130 \ ^{\circ}C$	<u>[1]</u> _	-	0.2	А
		$T_{sp} \le 145 \ ^{\circ}C$	-	-	0.2	А
V _R	reverse voltage		-	-	60	V
V _F	forward voltage	I _F = 0.2 A	-	540	600	mV
I _R	reverse current	$V_R = 60 V$	-	20	100	μA

[1] Device mounted on a ceramic Printed-Circuit Board (PCB), Al₂O₃, standard footprint.



200 mA low V_F MEGA Schottky barrier rectifier

2. Pinning information

Table 2.	Pinning		
Pin	Description	Simplified outline	e Graphic symbol
1	cathode	[1]	64
2	anode		1 1 2
			sym001

[1] The marking bar indicates the cathode.

3. Ordering information

Table 3. Orderi	ng informati	on	
Type number	Package		
	Name	Description	Version
PMEG6002EJ	SC-90	plastic surface-mounted package; 2 leads	SOD323F

4. Marking

Table 4. Marking codes	
Type number	Marking code
PMEG6002EJ	1P

5. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

$ \begin{array}{ c c c c c } \hline Symbol & Parameter & Conditions & Min & Max \\ \hline V_R & reverse voltage & T_j = 25 \ ^\circ C & - & 60 \\ \hline I_{F(AV)} & average forward current & square wave; \\ & \delta = 0.5; \\ f = 20 \ \text{kHz} & \hline T_{amb} \leq 130 \ ^\circ C & [1] & - & 0.2 \\ \hline T_{sp} \leq 145 \ ^\circ C & - & 0.2 \\ \hline I_{FRM} & repetitive peak forward \\ current & \delta \leq 0.25 & - & 0.2 \\ \hline I_{FSM} & non-repetitive peak \\ forward current & t_p = 8 \ ms & \hline P_{tot} & total power dissipation & T_{amb} \leq 25 \ ^\circ C & \hline [3][4] & - & 385 \\ \hline [3][5] & - & 605 \\ \hline \end{array} $,		
$ I_{F(AV)} \\ Average forward current \\ Ave$	nbol	Parameter	Conditions	Min	Max	Unit
$\begin{split} & \begin{array}{c} \delta = 0.5; \\ f = 20 \text{ kHz} \\ \hline T_{amb} \leq 130 \ ^{\circ}\text{C} & \begin{array}{c} 11 & - & 0.2 \\ \hline T_{sp} \leq 145 \ ^{\circ}\text{C} & - & 0.2 \\ \hline T_{sp} \leq 145 \ ^{\circ}\text{C} & - & 0.2 \\ \hline \end{array} \\ & \begin{array}{c} \text{I}_{\text{FRM}} & \begin{array}{c} \text{repetitive peak forward} \\ \text{current} & \begin{array}{c} t_p \leq 1 \text{ ms}; \\ \delta \leq 0.25 \end{array} & \begin{array}{c} - & 2.6 \\ \hline \end{array} \\ & \begin{array}{c} \text{I}_{\text{FSM}} & \begin{array}{c} \text{non-repetitive peak} \\ \text{forward current} \end{array} & \begin{array}{c} \text{square wave;} & \begin{array}{c} 21 \\ r_p = 8 \text{ ms} \end{array} & \begin{array}{c} 2.75 \\ \hline \end{array} \\ & \begin{array}{c} \text{P}_{\text{tot}} \end{array} & \begin{array}{c} \text{total power dissipation} \end{array} & \begin{array}{c} T_{amb} \leq 25 \ ^{\circ}\text{C} \end{array} & \begin{array}{c} 31/4 \\ \hline \end{array} & - & 385 \end{array} \end{split}$		reverse voltage	T _j = 25 °C	-	60	V
T _{sp} ≤ 145 °C0.2IFRMrepetitive peak forward current $t_p \le 1 \text{ ms};$ $\delta \le 0.25$ -2.6IFSMnon-repetitive peak forward currentsquare wave; $t_p = 8 \text{ ms}$ 2.75Ptottotal power dissipationT_{amb} \le 25 °C[3][4]-385	√)	average forward current	δ = 0.5;			
$ \begin{array}{c c} I_{FRM} & \mbox{repetitive peak forward} & t_p \leq 1 \mbox{ ms;} & - & 2.6 \\ current & \delta \leq 0.25 & - & 2.6 \\ \hline I_{FSM} & \mbox{non-repetitive peak} & \mbox{square wave;} & \box{$\frac{12}{2}$} & - & 2.75 \\ forward current & t_p = 8 \mbox{ ms} & - & 2.75 \\ \hline P_{tot} & \mbox{total power dissipation} & T_{amb} \leq 25 \ ^{\circ}\text{C} & \box{$\frac{13}{4}$} & - & 385 \\ \hline \end{array} $			$T_{amb} \le 130 \ ^{\circ}C$	<u>[1]</u> -	0.2	А
$\begin{array}{c} \text{current} & \delta \leq 0.25 \\ \\ I_{FSM} & \text{non-repetitive peak} & \text{square wave;} & 2 \\ \text{forward current} & t_p = 8 \text{ ms} \end{array} \qquad \begin{array}{c} 2.75 \\ \hline 2.7$			$T_{sp} \le 145 \ ^{\circ}C$	-	0.2	А
forward current $t_p = 8 \text{ ms}$ P_{tot} total power dissipation $T_{amb} \le 25 \ ^{\circ}C$ [3][4] -385	И			-	2.6	A
	Л		•	[2] _	2.75	A
[3][5] _ 605		total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	[3][4]	385	mW
<u></u>				[3][5]	695	mW
<u>[3][1]</u> - 1045				[3][1]	1045	mW

200 mA low V_F MEGA Schottky barrier rectifier

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Т _ј	junction temperature		-	150	°C
T _{amb}	ambient temperature		-55	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

[2] $T_j = 25 \ ^{\circ}C$ prior to surge.

[3] Reflow soldering is the only recommended soldering method.

- [4] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [5] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

6. Thermal characteristics

Table 6.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from	in free air	[1][2]			
	junction to ambient		[3] _	-	325	K/W
			<u>[4]</u> _	-	180	K/W
			[5] _	-	120	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point		<u>[6]</u> _	-	25	K/W

[1] For Schottky barrier diodes thermal runaway has to be considered, as in some applications the reverse power losses P_R are a significant part of the total power losses.

[2] Reflow soldering is the only recommended soldering method.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for cathode 1 cm².

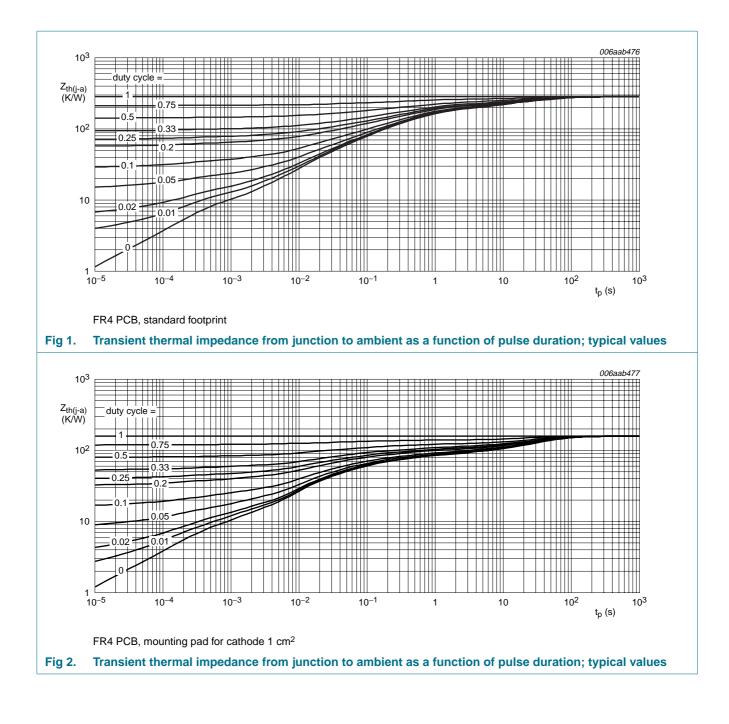
[5] Device mounted on a ceramic PCB, AI_2O_3 , standard footprint.

[6] Soldering point of cathode tab.

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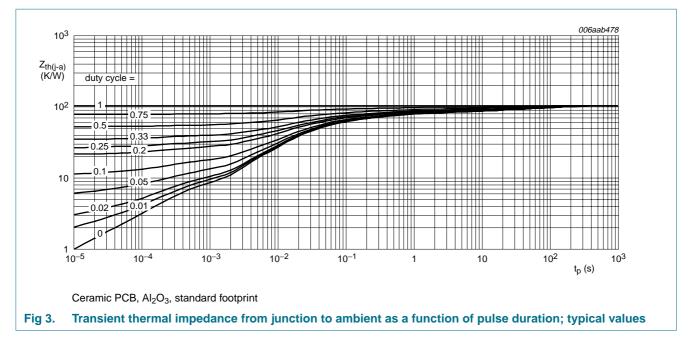
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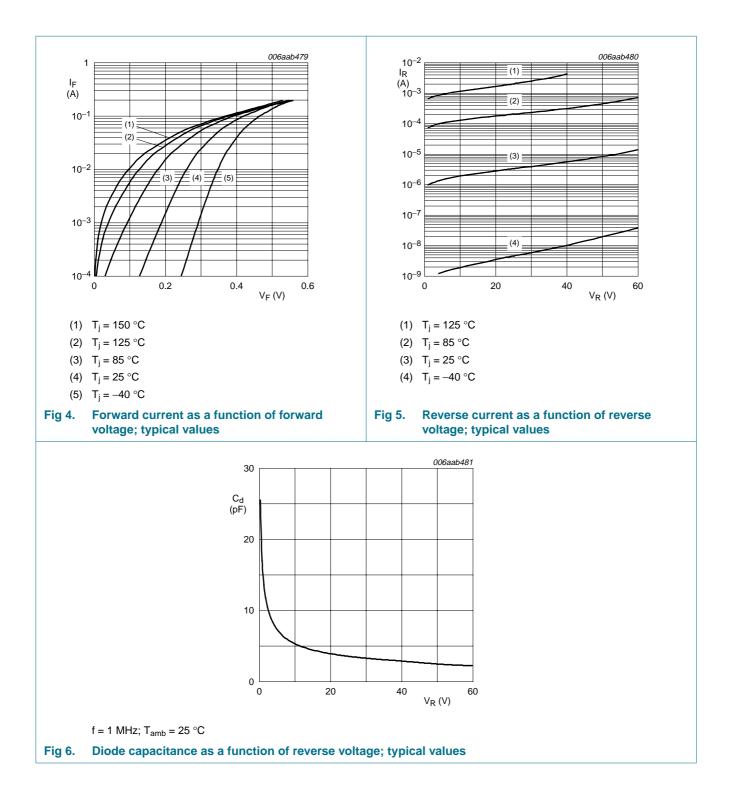
7. Characteristics

Table 7.Characteristics

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _F	forward voltage	I _F = 0.1 mA	-	130	170	mV
		$I_F = 1 \text{ mA}$	-	190	230	mV
		I _F = 10 mA	-	260	300	mV
	I _F = 100 mA	-	420	470	mV	
	I _F = 200 mA	-	540	600	mV	
I _R reverse current	V _R = 10 V	-	2	10	μA	
	V _R = 50 V	-	9	30	μA	
		V _R = 60 V	-	20	100	μA
C _d	diode capacitance	f = 1 MHz				
		V _R = 1 V	-	14	-	pF
		V _R = 10 V	-	6	-	pF
t _{rr}	reverse recovery time	e	<u>[1]</u> _	5	-	ns

[1] When switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω ; measured at I_R = 1 mA.

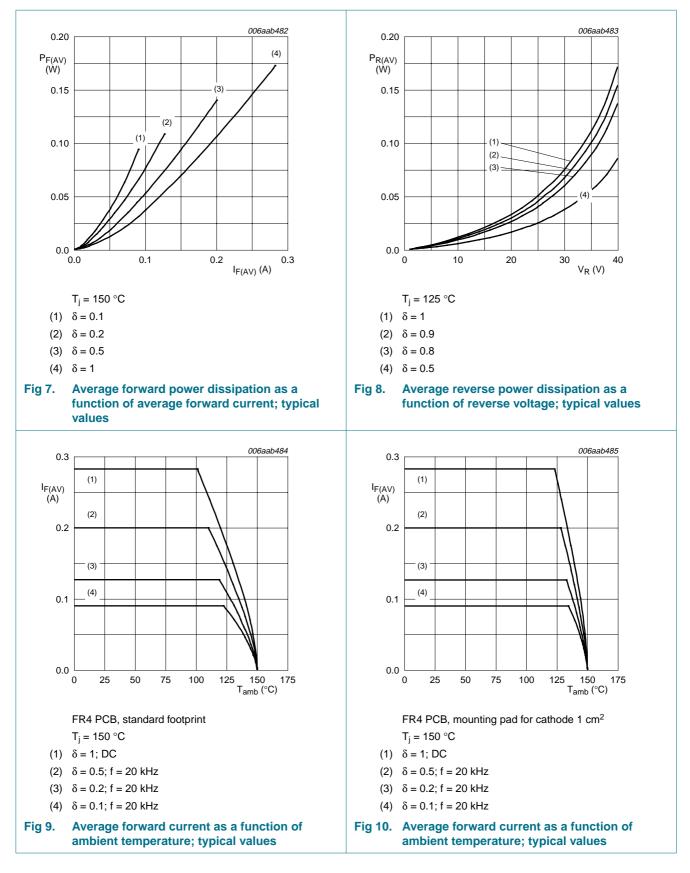
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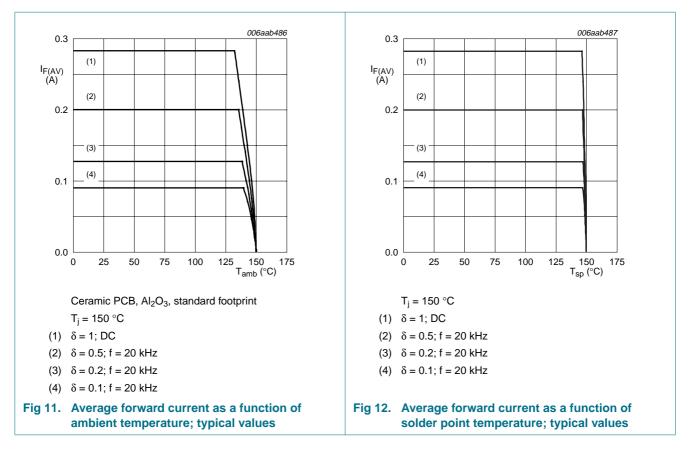
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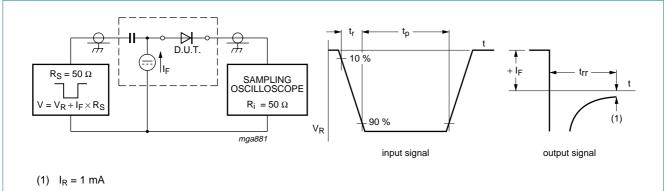
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Product data sheet

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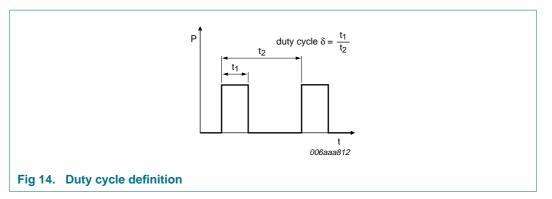
8. Test information



Input signal: reverse pulse rise time $t_r = 0.6$ ns; reverse voltage pulse duration $t_p = 100$ ns; duty cycle $\delta = 0.05$ Oscilloscope: rise time $t_r = 0.35$ ns

Fig 13. Reverse recovery time test circuit and waveforms

200 mA low V_F MEGA Schottky barrier rectifier



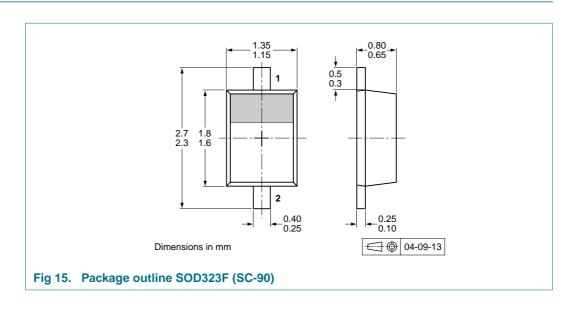
The current ratings for the typical waveforms as shown in Figure 9, 10, 11 and 12 are calculated according to the equations: $I_{F(AV)} = I_M \times \delta$ with I_M defined as peak current,

 $I_{RMS} = I_{F(AV)}$ at DC, and $I_{RMS} = I_M \times \sqrt{\delta}$ with I_{RMS} defined as RMS current.

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

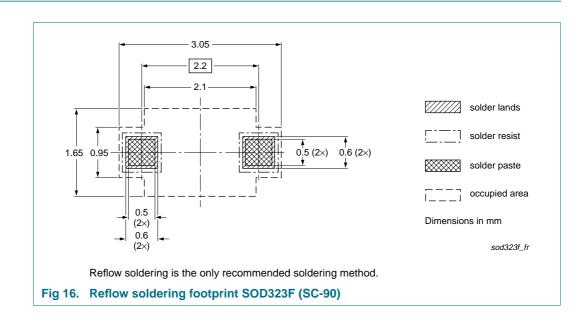


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10. Packing information

	king metho	ds ast three digits of the 12NC ordering code.[1]		
Type number Package Description Packing quantity				
			3000	10000
PMEG6002EJ	SOD323F	4 mm pitch, 8 mm tape and reel	-115	-135
[1] For further in	formation and	the availability of packing methods, see Section 14.		

11. Soldering



200 mA low V_F MEGA Schottky barrier rectifier

12. Revision history

Table 9. Revision his	tory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PMEG6002EJ_1	20090515	Product data sheet	-	-

200 mA low V_F MEGA Schottky barrier rectifier

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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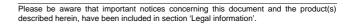
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Product data sheet

200 mA low V_F MEGA Schottky barrier rectifier

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